

Symbol	Parameter		Ratings	Units
V _{DSS}	Drain-to-Source Voltage		40	V
V _{GS}	Gate-to-Source Voltage		±20	V
	Drain Current - Continuous (V _{GS} =10) (Note 1)	T _C =25°C	240	•
D	Pulsed Drain Current	T _C = 25°C	See Figure 4	— A
E _{AS}	Single Pulse Avalanche Energy	(Note 2)	737	mJ
D	Power Dissipation		357	W
P _D	Derate Above 25°C		2.38	W/ºC
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 175	°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.42	°C/W
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	43	°C/W

Notes:

1: Current is limited by bondwire configuration.

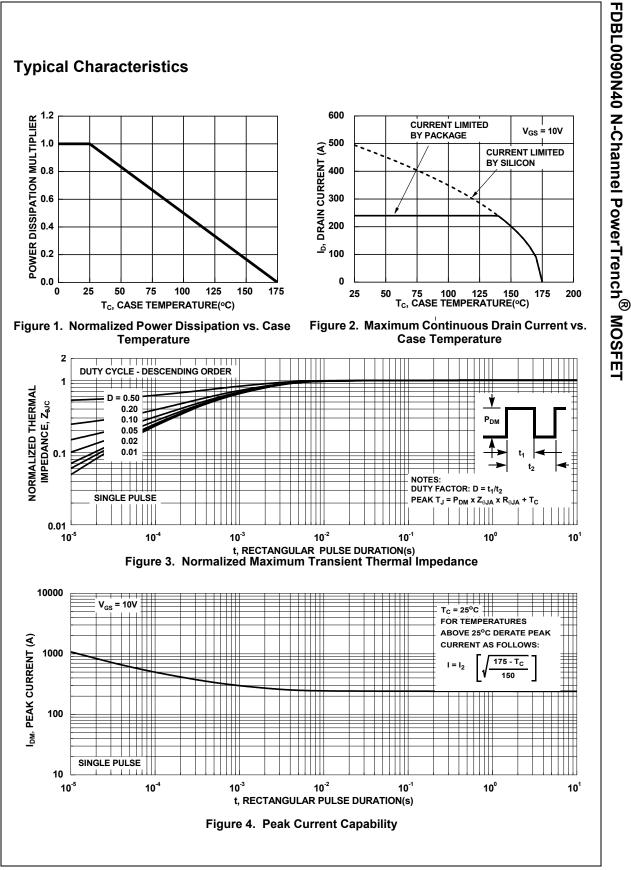
2: Starting $T_J = 25^{\circ}$ C, L = 0.36mH, $I_{AS} = 64A$, $V_{DD} = 40V$ during inductor charging and $V_{DD} = 0V$ during time in avalanche.

3: R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design, while R_{0JA} is determined by the board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

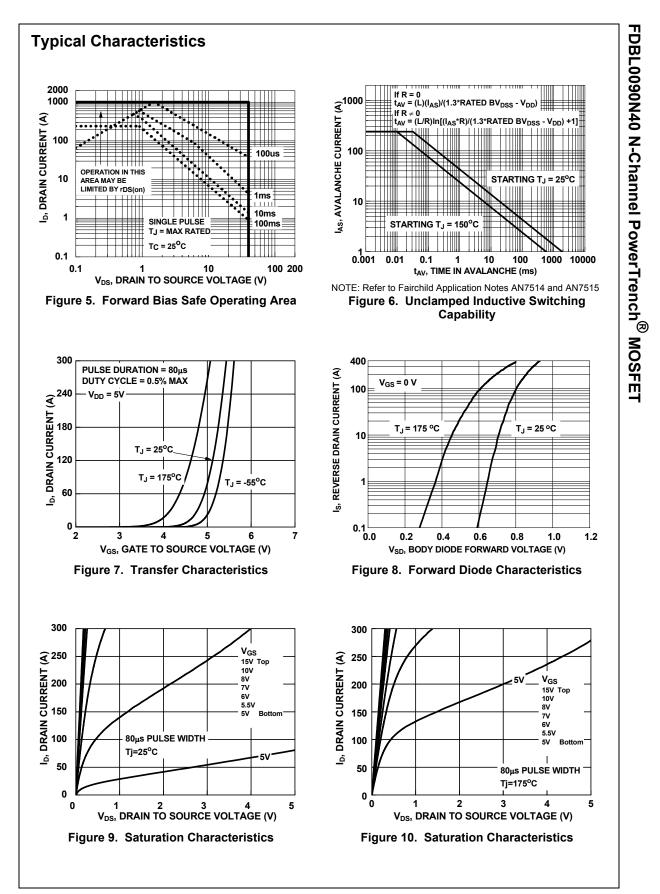
Package Marking and Ordering Information

Device Marking	Device	Package			
FDBL0090N40	FDBL0090N40	MO-299A	-	-	-

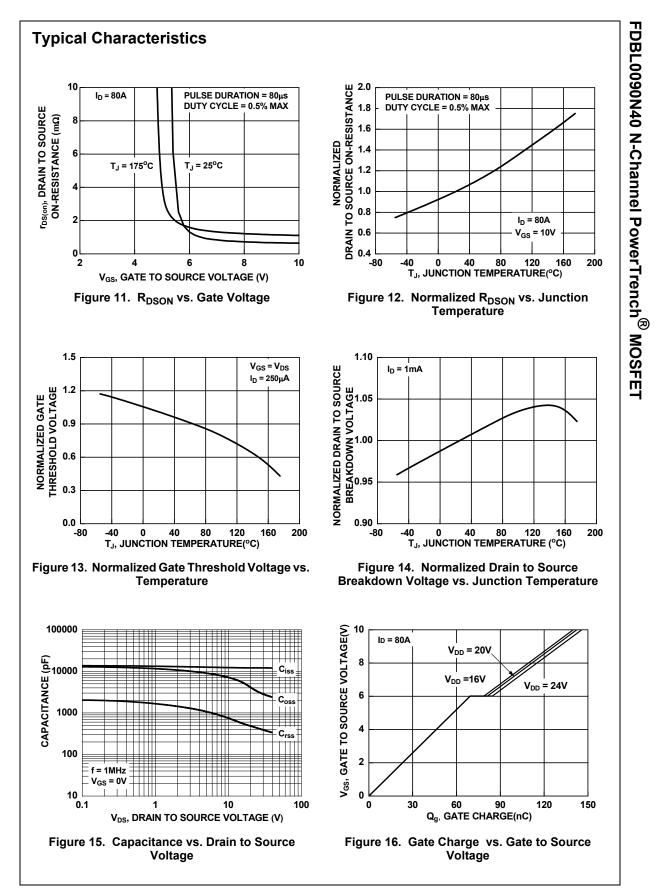
	Symbol	Parameter	Test	t Conditions	Min.	Тур.	Max.	Units
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	B _{VDSS}	Drain-to-Source Breakdown Voltage			40	-	-	V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	lnee	Drain-to-Source Leakage Current			-	-		μA
	.033	Ű		T _J = 175 ^o C (Note 4)	-	-		mA
	I _{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20V$		-	-	±100	nA
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$\begin{array}{c c c c c c c c c c c c c c c c c c c $	V	Cata to Source Threshold Voltage	<u> </u>	- 250 4	2.0	2.2	4.0	V
$\begin{array}{c c c c c c c c c c c c c c c c c c c $	VGS(th)	Gale to Source Threshold Voltage					-	-
Dynamic Characteristics C_{iss} Input Capacitance $V_{DS} = 25V, V_{GS} = 0V, f = 1000$ - pF C_{oss} Output Capacitance $V_{DS} = 25V, V_{GS} = 0V, f = 10Hz$ - 3260 - pF C_{rss} Reverse Transfer Capacitance $f = 1MHz$ - 3.3 - Ω $Q_g(ToT)$ Total Gate Charge at $10V$ $V_{GS} = 0$ to $10V$ $V_{DD} = 32V$ - 1444 188 nC $Q_{g(th)}$ Threshold Gate Charge $V_{GS} = 0$ to $2V$ $V_{DD} = 32V$ - 1444 188 nC $Q_{g(th)}$ Threshold Gate Charge $V_{GS} = 0$ to $2V$ $V_{DD} = 32V$ - 1444 188 nC Q_{gd} Gate-to-Source Gate Charge $V_{GS} = 0$ to $2V$ $V_{DD} = 80A$ - 22 26 nC Q_{gd} Gate-to-Drain "Miller" Charge - 16 - nC $Switching Characteristics$ $V_{DD} = 20V, I_D = 80A, V_{DD} = 20V, I_D = 80A, V_{DD} = 80A, P_{CS} = 10V, R_{GEN} = 6\Omega$ - 83 - ns $t_{d(off)}$ Turn-Off Delay $V_{GS} = $	R _{DS(on)}	Drain to Source On Resistance			-			
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3"Switching CharacteristicstonTurn-On Timet_d(on)Turn-On Delay162nst_d(off)Turn-Off DelayVDD = 20V, ID = 80A, VGS = 10V, RGEN = 6073-nst_d(off)Turn-Off DelayVGS = 10V, RGEN = 6050-nst_fFall Time279nst_offTurn-Off Time279ns	Qas	-		_	-		-	
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$ \begin{array}{c c} \mbox{t}_{d(off)} & \mbox{Turn-Off Delay} & \mbox{V}_{GS} = 10 \mbox{V}, \mbox{R}_{GEN} = 6 \Omega & - & 83 & - & ns \\ \hline \mbox{t}_{f} & \mbox{Fall Time} & - & 50 & - & ns \\ \hline \mbox{t}_{off} & \mbox{Turn-Off Time} & - & 279 & ns \\ \end{array} $	Q _{gd} Switchi	ng Characteristics					162	
Image: second	Q _{gd} Switchi t _{on} t _{d(on)}	ng Characteristics Turn-On Time Turn-On Delay			-	42	-	ns
t _{off} Turn-Off Time 279 ns	Q _{gd} Switchi t _{on} t _{d(on)} t _r	ng Characteristics Turn-On Time Turn-On Delay Rise Time			-	42 73	-	ns ns
	Q _{gd} Switchi t _{on} t _{d(on)} t _r t _{d(off)}	ng Characteristics Turn-On Time Turn-On Delay Rise Time Turn-Off Delay			-	42 73 83	-	ns ns ns
Drain Source Diade Characteristics	Q _{gd} Switchi t _{on} t _{d(on)} t _r t _{d(off)} t _f	ng Characteristics Turn-On Time Turn-On Delay Rise Time Turn-Off Delay Fall Time			- - -	42 73 83 50	-	ns ns ns ns
	Q _{gd} Switchi	ng Characteristics					400	
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$l_{00} = 80A V_{00} = 0V$ 1.25 V	Q_{gd} Switchi t_{on} $t_{d(on)}$ t_r $t_{d(off)}$ t_f t_{off}	ng Characteristics Turn-On Time Turn-On Delay Rise Time Turn-Off Delay Fall Time Turn-Off Time	V _{GS} = 10V,	R _{GEN} = 6Ω		42 73 83 50	- - - 279	ns ns ns ns
V_{SD} Source-to-Drain Diode Voltage $\frac{I_{SD} = 80A, V_{GS} = 0V 1.25 V}{I_{SD} = 40A, V_{GS} = 0V 1.25 V}$	Q_{gd} Switchi t_{on} $t_{d(on)}$ t_r $t_{d(off)}$ t_f t_{off} Drain-S	ng Characteristics Turn-On Time Turn-On Delay Rise Time Turn-Off Delay Fall Time Turn-Off Time cource Diode Characteristics	V _{GS} = 10V,	R _{GEN} = 6Ω _{GS} = 0V		42 73 83 50 -	- - 279 1.25	ns ns ns ns V
$ \begin{array}{c c c c c c c } V_{SD} & Source-to-Drain Diode Voltage & \hline I_{SD} = 80A, V_{GS} = 0V & - & - & 1.25 & V \\ \hline I_{SD} = 40A, V_{GS} = 0V & - & - & 1.2 & V \\ \hline I_{F} = 80A, dI_{SD}/dt = 100A/\mu s, & - & 111 & 129 & ns \\ \hline \end{array} $	Q_{gd} Switchi t_{on} $t_{d(on)}$ t_r $t_{d(off)}$ t_f t_{off} Drain-S	ng Characteristics Turn-On Time Turn-On Delay Rise Time Turn-Off Delay Fall Time Turn-Off Time cource Diode Characteristics Source-to-Drain Diode Voltage	V _{GS} = 10V,	$R_{GEN} = 6\Omega$ GS = 0V $V_{GS} = 0V$		42 73 83 50 - -	- - 279 1.25 1.2	ns ns ns ns v V



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